30V N&P-Channel Trench Power MOSFET

General Description

The SJP30NP493 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as ±4.5V. This device is suitable for use as a wide variety of applications.

Features

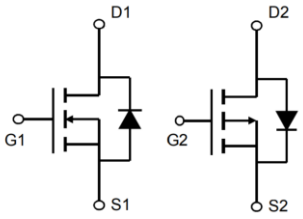
- Low Gate Charge
- High Power and current handing capability
- Lead free product is acquired

Application

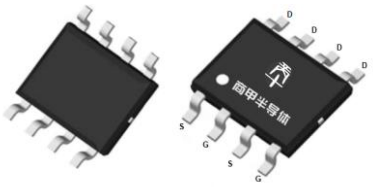
- Battery Protection
- Power Management
- Load Switch

Key Performance Parametes

Parameter	Value	Value	Unit
V_{DS}	30	-30	V
$R_{DS(ON)\_TYP}$	16.3	32	mΩ
I_D	7	-5.6	A
Q_G	8.3	16	nC



Schematic Diagram



SOP-8 top&bottom view

RoHS

Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJP30NP493	SJP30NP493	SOP-8	Tape	\	\	4000 Pcs

Table 1. Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	N Limit	P Limit	Unit
V_{DS}	Drain-Source Voltage (V_{GS}=0V)	30	-30	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	±20	±20	V
I_D	Drain Current-Continuous(T_A=25℃)	7	-5.6	A
	Drain Current-Continuous(T_A =100℃)	4.4	-3.5	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	28	-22.4	A
P_D	Maximum Power Dissipation(T_A =25℃)	1.6	2	W
	Maximum Power Dissipation(T_A =100℃)	0.6	0.8	W
E_{AS}	Avalanche energy (Note 2)	25	30	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150		℃

Table 2. Thermal Characteristic

Symbol	Parameter	N Max	P Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to- Ambient	80	63	℃/W

Table 3. N-Channel Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V T_J=25℃			1	μA
		V_{DS}=30V, V_{GS}=0V T_J=125℃			100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0		2.5	V
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=3A		6		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V, I_D=3A T_J=25℃		16.3	20.4	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=4.5V, I_D=2A T_J=25℃		25.7	34.2	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=15V,V_{GS}=0V, f=1.0MHz		441		pF
C_{oss}	Output Capacitance			61		pF
C_{rss}	Reverse Transfer Capacitance			48		pF
Rg	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1.0MHz		1.1		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=10V, V_{DS}=15V, R_L=5Ω, R_{GEN}=3Ω		2.8		nS
t_r	Turn-on Rise Time			6		nS
$t_{d(off)}$	Turn-Off Delay Time			16		nS
t_f	Turn-Off Fall Time			3.2		nS
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=3A		8.3		nC
Q_{gs}	Gate-Source Charge			1.3		nC
Q_{gd}	Gate-Drain Charge			1.4		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				7	A
V_{SD}	Forward on Voltage (Note 3)	V_{GS}=0V, I_S=3A			1.2	V
t_{rr}	Reverse Recovery Time	I_F=3A, dI/dt=500A/μs		10		ns
Q_{rr}	Reverse Recovery Charge	I_F=3A, dI/dt=500A/μs		5		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=30V,V_G=10V, Rg=25Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

N-Channel Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

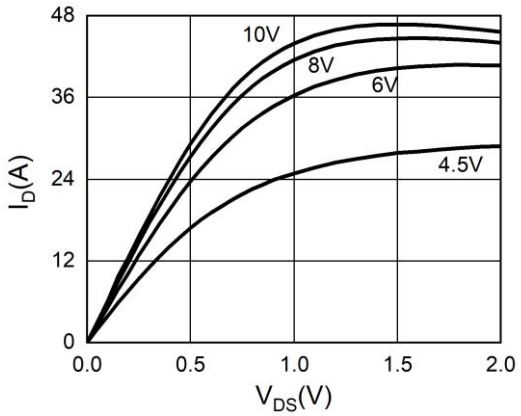


Figure 2. Transfer Characteristics

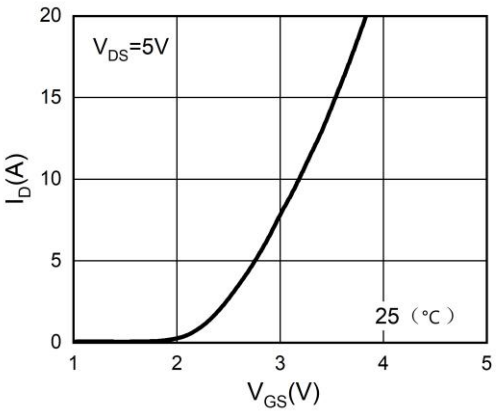


Figure 3. Power Dissipation

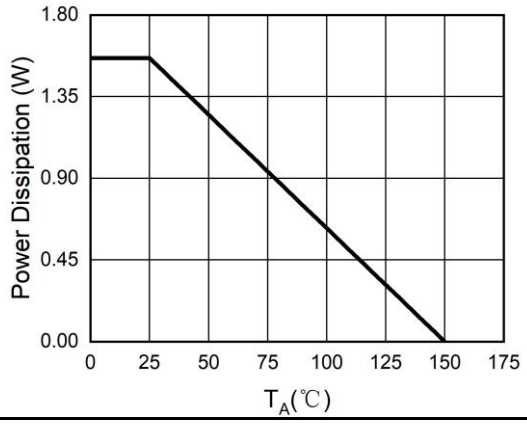


Figure 4. Drain Current

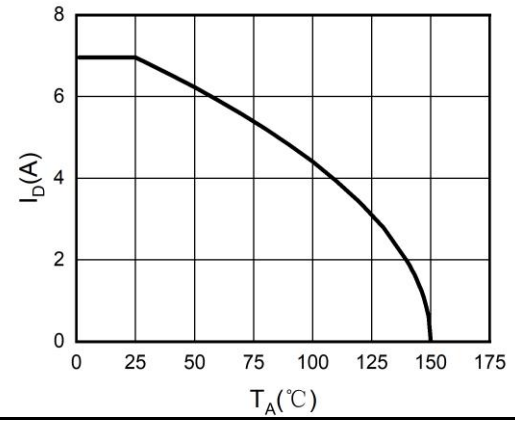


Figure 5. BV_{DSS} vs Junction Temperature

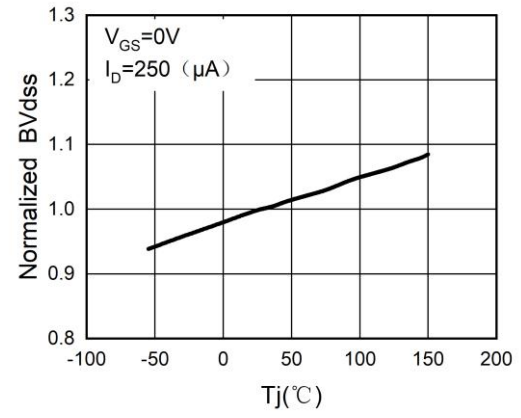
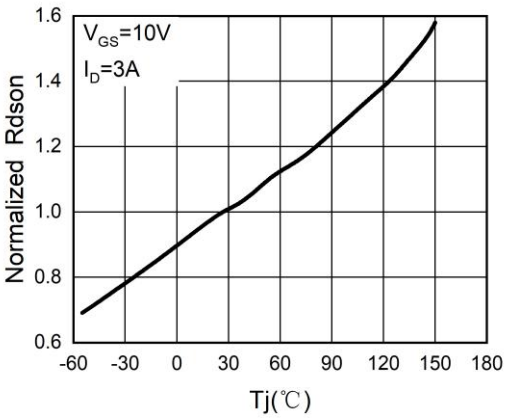


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



N-Channel Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Gate Charge Waveforms

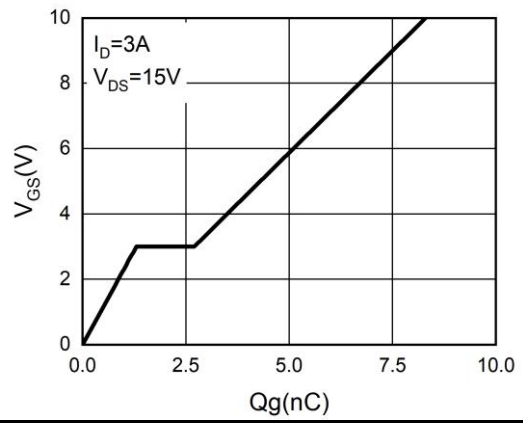


Figure 8. Capacitance

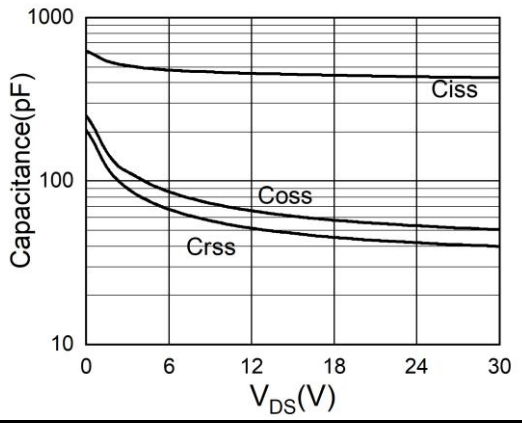


Figure 9. Body-Diode Characteristics

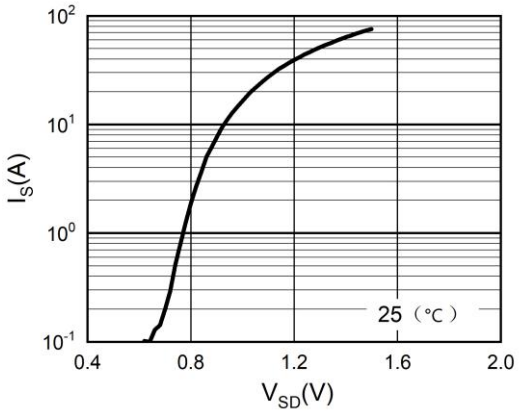


Figure 10. Maximum Safe Operating Area

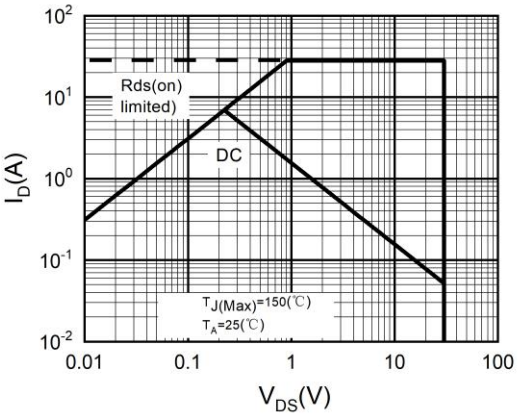


Table 4. P-Channel Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=-250μA	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V, V_{GS}=0V T_J=25℃			-1	μA
		V_{DS}=-30V, V_{GS}=0V T_J=125℃			-100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	-1		-2.5	V
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-2A		4.6		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=-10V, I_D=-2A T_J=25℃		32	40	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=-4.5V, I_D=-1.52A T_J=25℃		43.5	57.9	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=-15V,V_{GS}=0V, f=1.0MHz		594		pF
C_{oss}	Output Capacitance			80		pF
C_{rss}	Reverse Transfer Capacitance			63		pF
Rg	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1.0MHz		6.4		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=-10V, V_{DS}=-15V, R_L=7.5Ω, R_{GEN}=3Ω		7.5		nS
t_r	Turn-on Rise Time			5.5		nS
$t_{d(off)}$	Turn-Off Delay Time			19		nS
t_f	Turn-Off Fall Time			7		nS
Q_g	Total Gate Charge	V_{GS}=-10V, V_{DS}=-15V, I_D=-2A		16		nC
Q_{gs}	Gate-Source Charge			2		nC
Q_{gd}	Gate-Drain Charge			4		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				-5.6	A
V_{SD}	Forward on Voltage (Note 3)	V_{GS}=0V, I_S=-2A			-1.2	V
t_{rr}	Reverse Recovery Time	I_F=-2A, dI/dt=500A/μs		15		ns
Q_{rr}	Reverse Recovery Charge	I_F=-2A, dI/dt=500A/μs		10		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=-30V,V_G=-10V, Rg=25Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

P-Channel Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

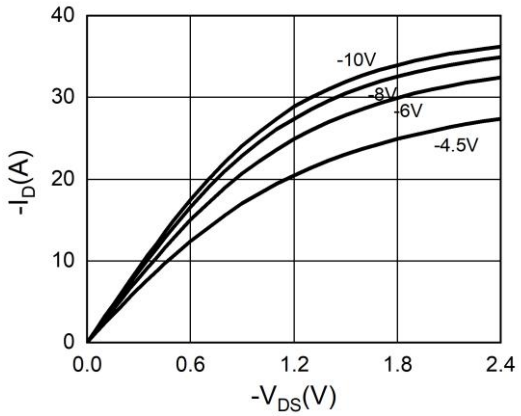


Figure 2. Transfer Characteristics

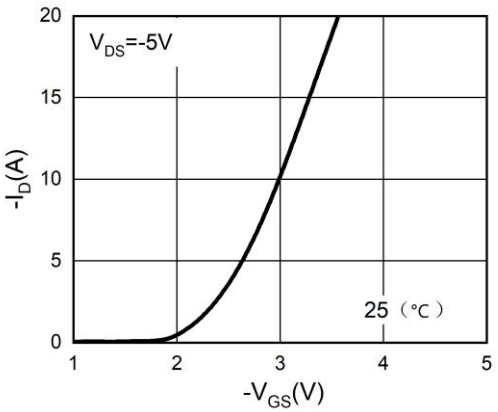


Figure 3. Power Dissipation

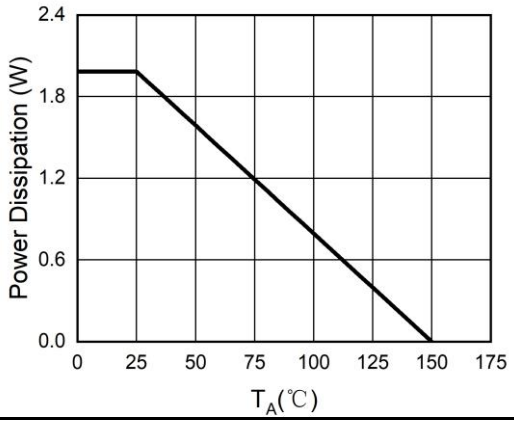


Figure 4. Drain Current

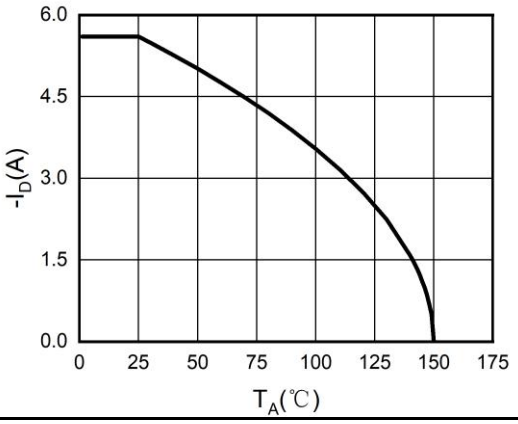


Figure 5. BV_{DSS} vs Junction Temperature

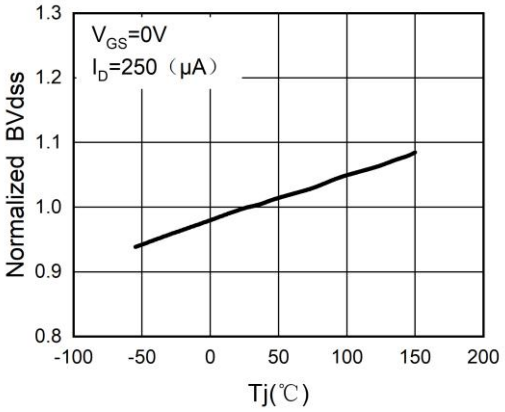
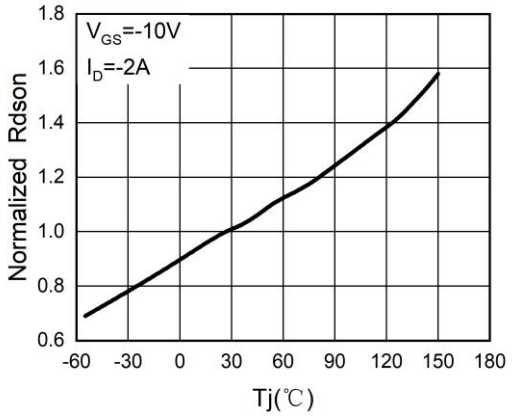


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



P-Channel Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Gate Charge Waveforms

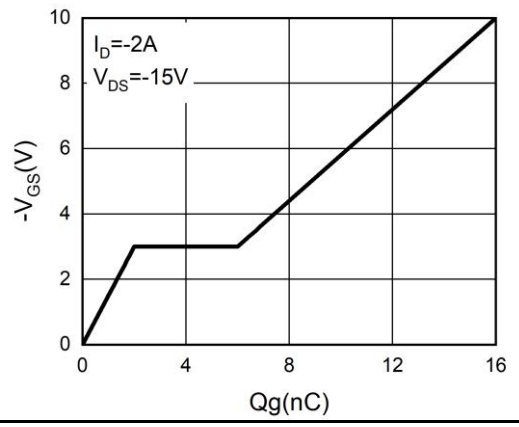


Figure 8. Capacitance

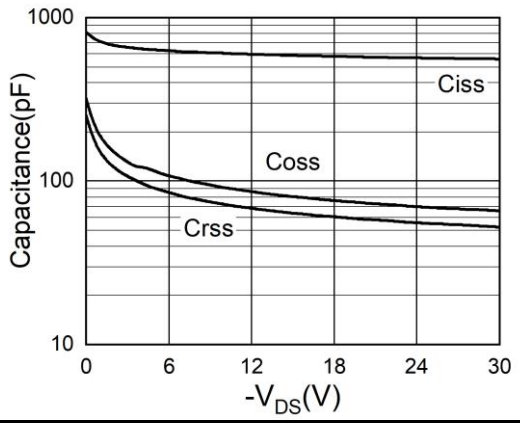


Figure 9. Body-Diode Characteristics

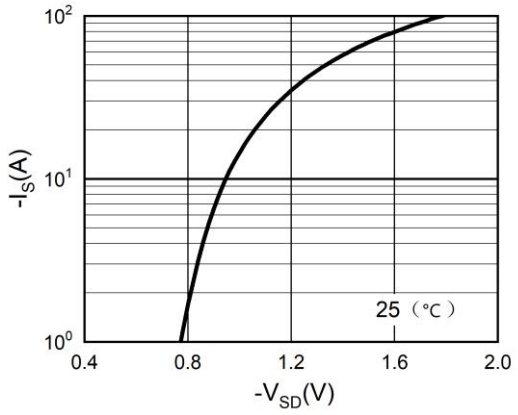
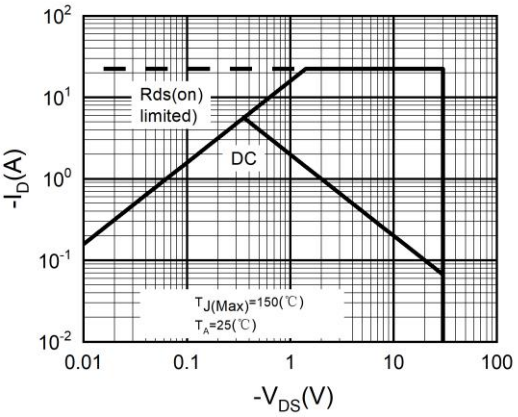
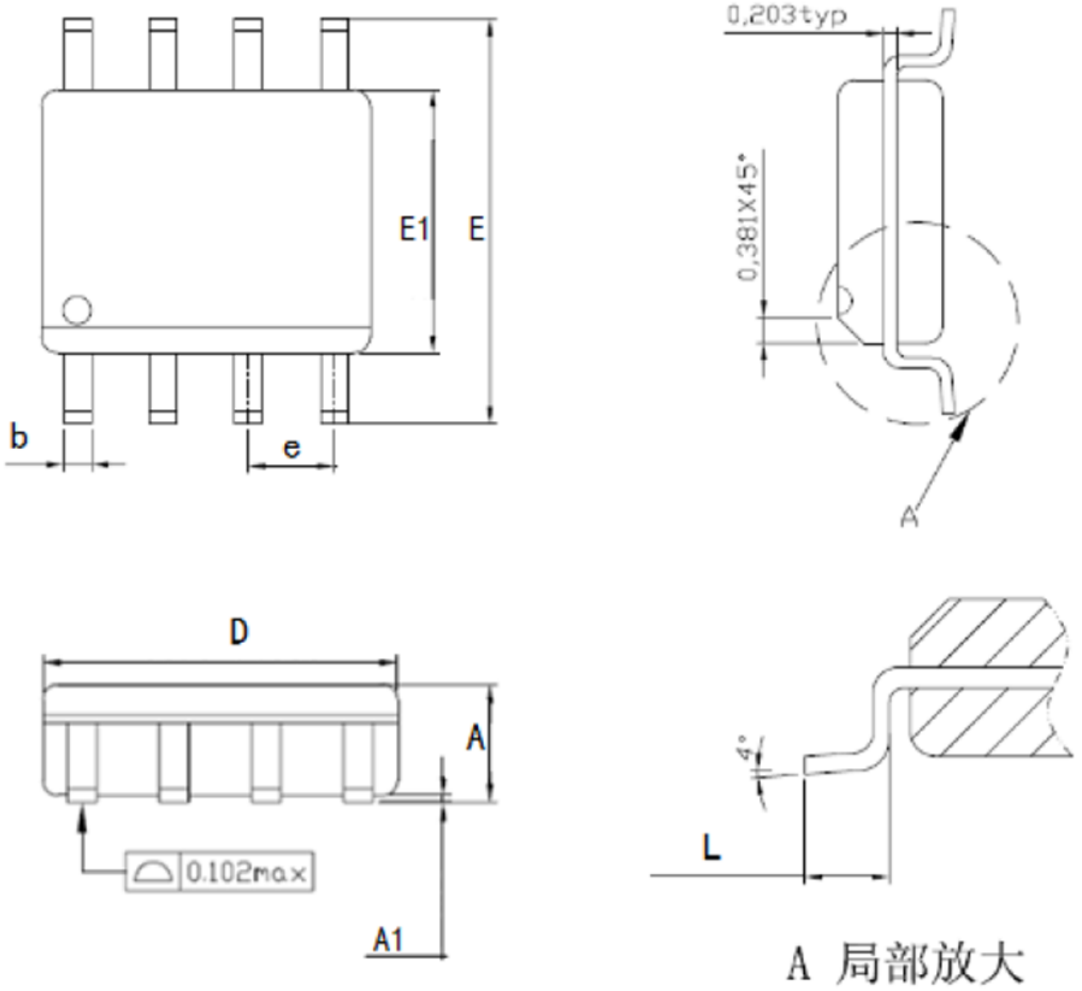


Figure 10. Maximum Safe Operating Area



SOP-8 Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max
A	1.35	1.55	1.75
A1	0.1	0.15	0.2
b	0.346	0.406	0.466
D	4.8	4.89	4.98
E	5.75	6.00	6.25
E1	3.81	3.90	3.99
e	1.27TYP		
L	0.406	0.838	1.27

Attention

This product described in this document can not be used in life support devices or systems, aircraft's control systems, and other applications whose failure can be reasonably expected to result in serious physical and/or material damage，apart from that when an application agreement is signed between customer and Wuxi Shangjia Semiconductor.

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